

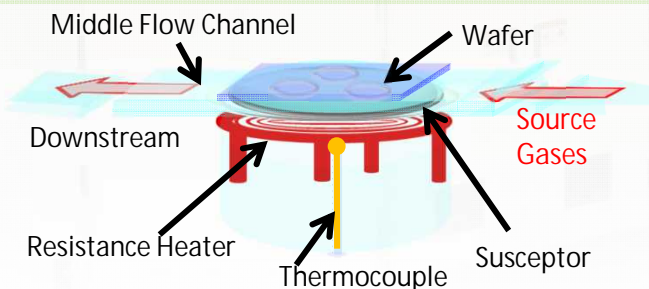


## SR4000 HT Configuration

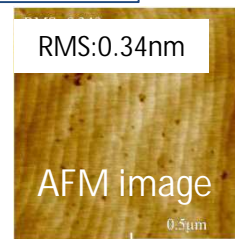
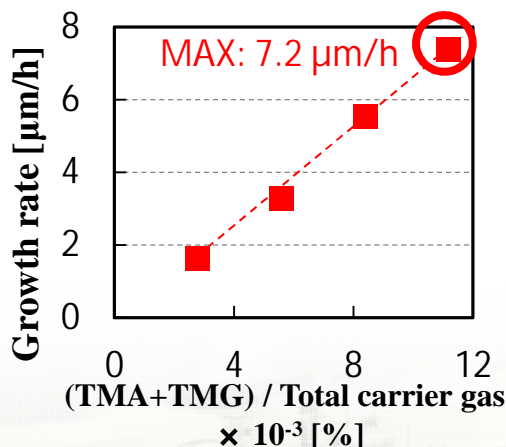
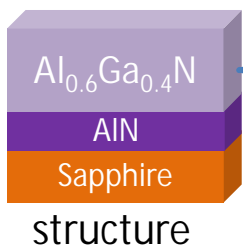
Target : LED (from Green to UV), LD, Nitride E-Devices

Specification :

1. Wafer Size : 4" × 1, 2" × 3
2. Heating : up to 1300 → High Quality AlN Growth
3. Growth at 10 kPa–100 kPa → Control of carbon concentration
4. 3-layer horizontal laminar flow → Control of gas phase reaction
5. Correspond to UL regulation
6. Option: In-Situ monitor, Gas concentration monitor, etc.



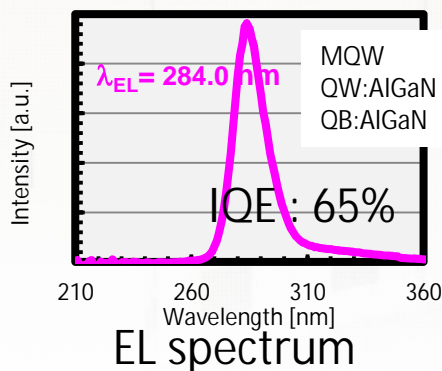
## High Growth Rate AlGa<sub>0.4</sub>N (Al>0.5)



n-Al<sub>0.6</sub>Ga<sub>0.4</sub>N Resistibility  
< 2.2 × 10<sup>-2</sup> Ω cm @ 7.2 μm/h

\*Presented at the ISGN-6 (The 6<sup>th</sup> International Symposium on Growth of III-Nitrides)

## DUV LED Electro-Luminescence



\*collaboration with ITRI (Industrial Technology Research Institute of Taiwan)